
State-of-the-Art Program on Compound Semiconductors 58 (SOTAPOCS 58)

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Sponsoring Division:**Electronics and Photonics**Published by
The Electrochemical Society65 South Main Street, Building D
Pennington, NJ 08534-2839, USA

tel 609 737 1902

fax 609 737 2743

www.electrochem.org

ecstransactions™**Vol. 69, No. 14**

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Published by:

The Electrochemical Society
65 South Main Street
Pennington, New Jersey 08534-2839, USA

Telephone 609.737.1902
Fax 609.737.2743
e-mail: ecs@electrochem.org
Web: www.electrochem.org

ISSN 1938-6737 (online)
ISSN 1938-5862 (print)
ISSN 2151-2051 (cd-rom)

ISBN 978-1-62332-321-9 (CD-ROM)
ISBN 978-1-60768-679-8 (PDF)

Printed in the United States of America.

ECS Transactions, Volume 69, Issue 14

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Table of Contents

<i>Preface</i>	<i>iii</i>
----------------	------------

**Chapter 1
Semiconductor Growth & Processing**

CMOS Compatible <i>in-Situ</i> N-Type Doping of Ge Using New Generation Doping Agents P(MH ₃) ₃ and As(MH ₃) ₃ (M=Si, Ge) <i>C. Xu, J. D. Gallagher, C. Senaratne, P. Sims, J. Kouvettakis, J. Menendez</i>	3
Propagation of Nanopores and Formation of Nanoporous Domains during Anodization of n-InP in KOH <i>D. N. Buckley, R. P. Lynch, N. Quill, C. O'Dwyer</i>	17
Towards Electrochemical Fabrication of Free-Standing Indium Phosphide Nanofilms <i>N. Quill, C. O'Dwyer, D. N. Buckley, R. P. Lynch</i>	33

**Chapter 2
Compound Semiconductor Characterization**

Terahertz Spectroscopy: Studying Carrier Dynamics in Semiconductor Nanostructures <i>L. V. Titova, S. Xu, J. M. Baribeau, D. J. Lockwood, F. Hegmann</i>	51
---	----

**Chapter 3
Optoelectronics**

Recent Developments in Mercury Cadmium Telluride IR Detector Technology <i>J. Antoszewski, N. D. Akhavan, G. Umana-Membreño, R. Gu, W. Lei, L. Faraone</i>	61
Flexible Graphene Electrode-Based Organic Photovoltaics with Record-High Efficiency <i>H. Park, S. Chang, X. Zhou, J. Kong, T. Palacios, S. Gradiček</i>	77

Crystalline Tetrahedral Phases $\text{Al}_{1-x}\text{B}_x\text{PSi}_3$ and $\text{Al}_{1-x}\text{B}_x\text{AsT}_3$ ($T = \text{Si}, \text{Ge}$) Via Reactions of $\text{Al}(\text{BH}_4)_3$ and $\text{M}(\text{TH}_3)_3$ ($\text{M} = \text{P}, \text{As}$) <i>P. Sims, T. Aoki, J. Menendez, J. Kouvettakis</i>	83
--	----

Chapter 4 Nitride Materials & Devices

(Invited) From MRTA to SMRTA: Improvements in Activating Implanted Dopants in GaN <i>J. D. Greenlee, B. Feigelson, T. J. Anderson, J. K. Hite, K. D. Hobart, F. J. Kub</i>	97
---	----

Study of the Effects of GaN Buffer Layer Quality on the dc Characteristics of AlGaN/GaN High Electron Mobility Transistors <i>S. Ahn, W. Zhu, C. Dong, Y. H. Hwang, B. J. Kim, F. Ren, S. J. Pearson, A. G. Lind, K. S. Jones, I. Kravchenko</i>	103
---	-----

Chapter 5 Poster Session

Effect of Buffer Oxide Etchant (BOE) on Ti/Al/Ni/Au Ohmic Contacts for AlGaN/GaN Based HEMT <i>Y. H. Hwang, S. Ahn, C. Dong, W. Zhu, B. J. Kim, F. Ren, A. G. Lind, K. S. Jones, S. J. Pearson, I. Kravchenko</i>	111
--	-----

Chapter 6 Radiation Effects

Simulating RF Performance of Proton Irradiated AlGaN/GaN High Electron Mobility Transistors (HEMT) <i>S. Mukherjee, E. Patrick, M. E. Law</i>	121
--	-----

Study on Effect of Proton Irradiation Energy in AlGaN/GaN Metal-Oxide Semiconductor High Electron Mobility Transistors <i>S. Ahn, C. Dong, W. Zhu, B. J. Kim, Y. H. Hwang, F. Ren, S. J. Pearson, G. Yang, J. Kim, I. Kravchenko</i>	129
---	-----

Cathodoluminescence Studies of Gamma-Irradiation Effects on AlGaN/GaN High Electron Mobility Transistors (HEMTs)	137
--	-----

A. Yadav, M. Antia, E. Flitsiy, L. Chernyak, I. Lubomirsky, J. Salzman

Chapter 7 **Group IV Materials and Devices**

Enhanced Performance Designs of Group-IV Light Emitting Diodes for Mid IR Photonic Applications	147
---	-----

J. D. Gallagher, C. Senaratne, C. Xu, P. M. Wallace, J. Menendez, J. Kouvettakis

Doping of Direct Gap $\text{Ge}_{1-y}\text{Sn}_y$ Alloys to Attain Electroluminescence and Enhanced Photoluminescence	157
---	-----

C. L. Senaratne, J. D. Gallagher, C. Xu, P. Sims, J. Menendez, J. Kouvettakis

Author Index	165
--------------	-----